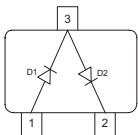


Silicon Low Leakage Diode

- Low-leakage applications
- Medium speed switching times
- Series pair configuration
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



BAV199



Type	Package	Configuration	Marking
BAV199	SOT23	series	JYs

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	80	V
Peak reverse voltage	V_{RM}	85	
Forward current	I_F	200	mA
Non-repetitive peak surge forward current	I_{FSM}		A
$t = 1 \mu\text{s}$		4.5	
$t = 1 \text{ s}$		0.5	
Total power dissipation BAV199, $T_S \leq 31^\circ\text{C}$	P_{tot}	330	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

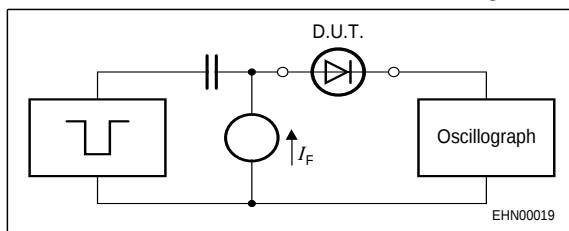
Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾ BAV199	R_{thJS}	≤ 360	K/W

¹⁾Pb-containing package may be available upon special request

²⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage $I_{(BR)} = 100 \mu A$	$V_{(BR)}$	85	-	-	V
Reverse current $V_R = 75 V$ $V_R = 75 V, T_A = 150 ^\circ C$	I_R	- -	- -	5 80	nA
Forward voltage $I_F = 1 mA$ $I_F = 10 mA$ $I_F = 50 mA$ $I_F = 150 mA$	V_F	- - - -	- - - -	900 1000 1100 1250	mV
AC Characteristics					
Diode capacitance $V_R = 0 V, f = 1 MHz$	C_T	-	2	-	pF
Reverse recovery time $I_F = 10 mA, I_R = 10 mA$, measured at $I_R = 1mA$, $R_L = 100 \Omega$	t_{rr}	-	0.6	1.5	μs

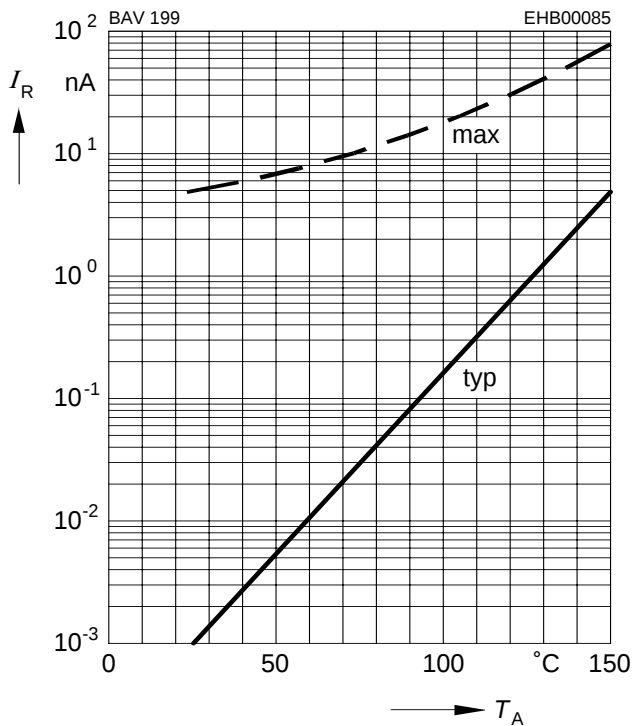
Test circuit for reverse recovery time


Pulse generator: $t_p = 10 \mu\text{s}$, $D = 0.05$, $t_r = 0.6 \text{ ns}$,
 $R_i = 50 \Omega$

Oscilloscope: $R = 50 \Omega$, $t_r = 0.35 \text{ ns}$, $C \leq 1 \text{ pF}$

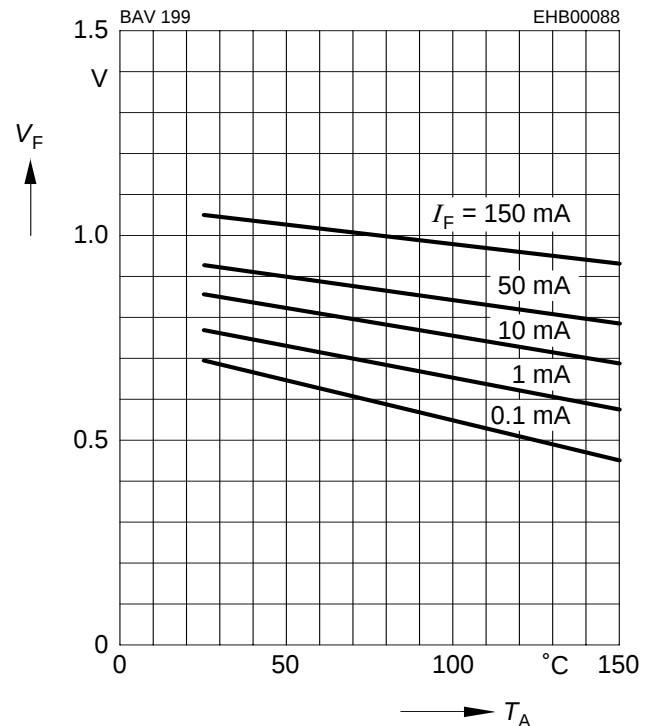
Reverse current $I_R = f(T_A)$

$V_R = 70V$



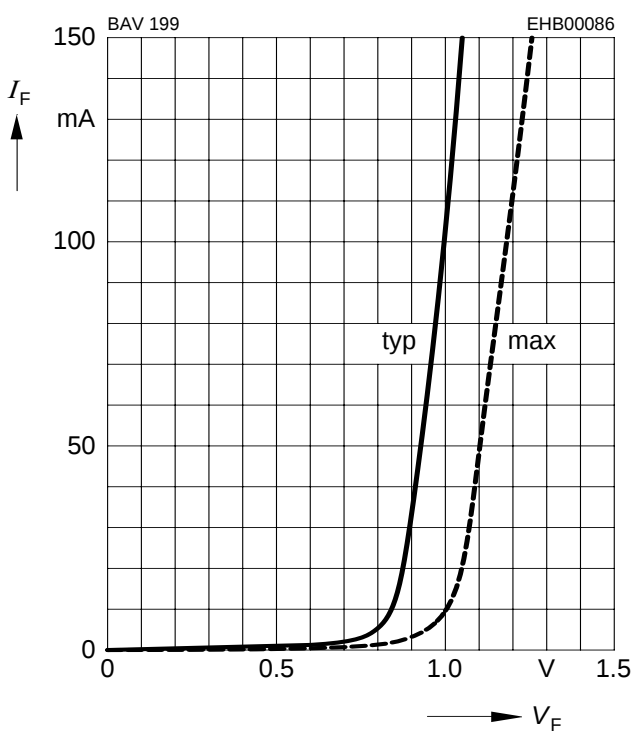
Forward Voltage $V_F = f(T_A)$

$I_F = \text{Parameter}$



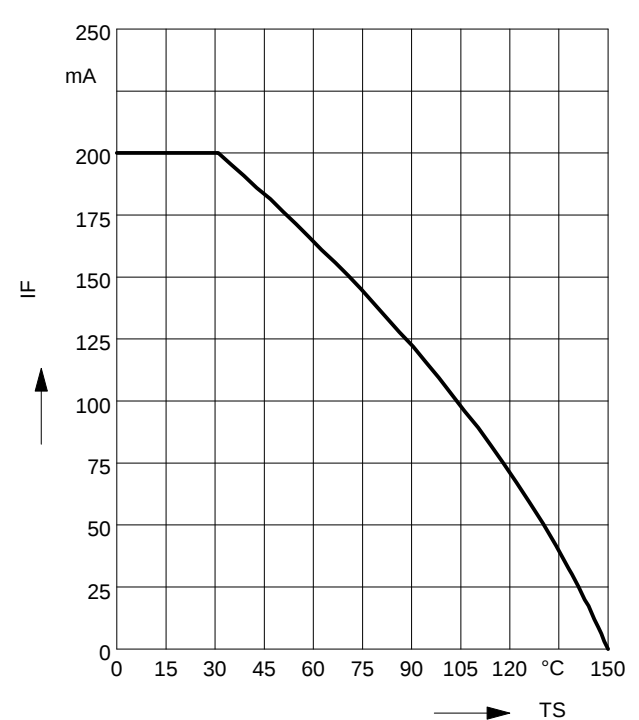
Forward current $I_F = f(V_F)$

$T_A = 25^\circ\text{C}$

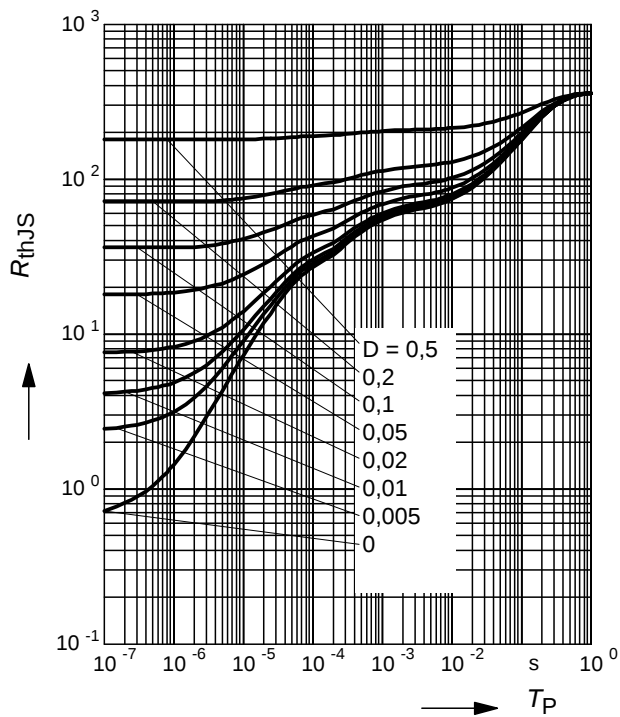


Forward current $I_F = f(T_S)$

BAV199

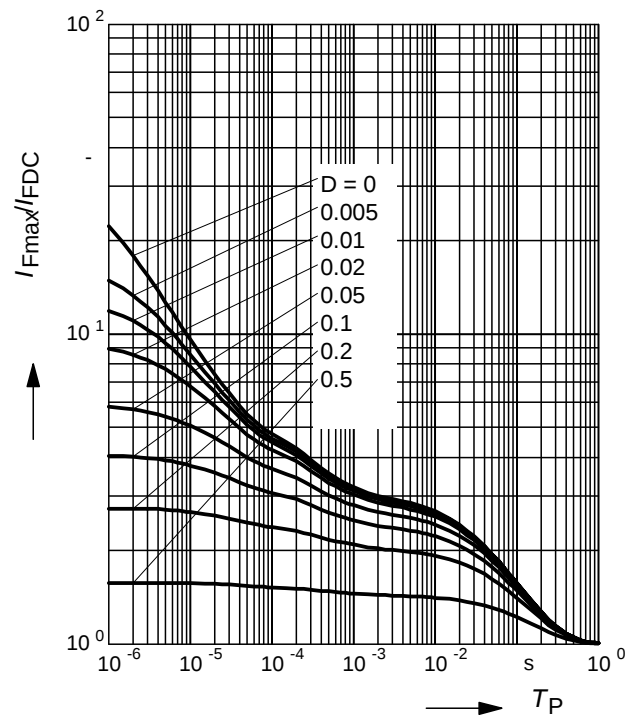


Permissible Puls Load $R_{thJS} = f(t_p)$

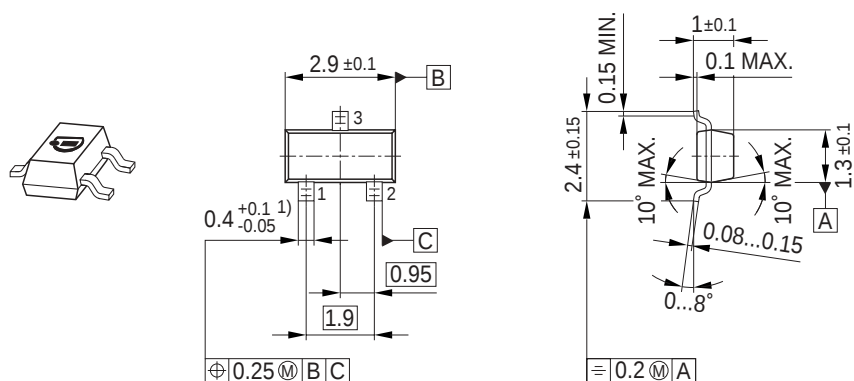


Permissible Pulse Load

$$I_{Fmax}/I_{FDC} = f(t_p)$$

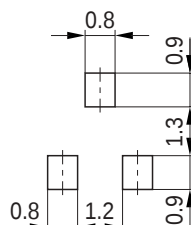


Package Outline

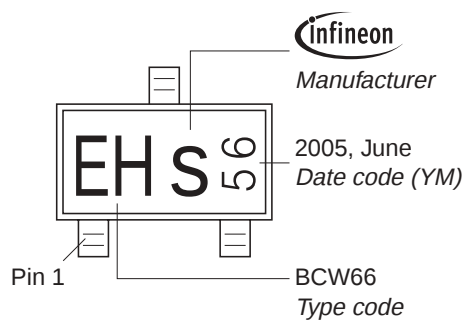


1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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